













SCES204Q - APRIL 1999 - REVISED MARCH 2017

# SN74LVC2G125 Dual Bus Buffer Gate With 3-State Outputs

#### **Features**

- ESD Protection Exceeds JESD 22
  - 2000-V Human-Body Model
  - 1000-V Charged-Device Model
- Available in the Texas Instruments NanoFree™ Package
- Supports 5-V V<sub>CC</sub> Operation
- Inputs Accept Voltages to 5.5 V
- Max  $t_{pd}$  of 4.3 ns at 3.3 V
- Low Power Consumption, 10-µA Max I<sub>CC</sub>
- ±24-mA Output Drive at 3.3 V
- Typical V<sub>OLP</sub> (Output Ground Bounce)  $< 0.8 \text{ V at V}_{CC} = 3.3 \text{ V}, T_A = 25^{\circ}\text{C}$
- Typical V<sub>OHV</sub> (Output V<sub>OH</sub> Undershoot)  $> 2 \text{ V at V}_{CC} = 3.3 \text{ V}, T_A = 25^{\circ}\text{C}$
- Ioff Supports Live Insertion, Partial-Power-Down Mode, and Back-Drive Protection
- Can Be Used as a Down Translator to Translate Inputs From a Max of 5.5 V Down to the V<sub>CC</sub> Level
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II

## 2 Applications

- Cable Modem Termination Systems
- High-Speed Data Acquisition and Generation
- Military: Radars and Sonars
- Motor Controls: High-Voltage
- **Power Line Communication Modems**
- SSDs: Internal or External
- Video Broadcasting and Infrastructure: Scalable **Platforms**
- Video Broadcasting: IP-Based Multi-Format Transcoders
- Video Communications Systems

## 3 Description

The SN74LVC2G125 device is a dual bus buffer gate, designed for 1.65-V to 5.5-V V<sub>CC</sub> operation. This device features dual line drivers with 3-state outputs. The outputs are disabled when the associated output-enable (OE) input is high.

NanoFree™ package technology is a major breakthrough in IC packaging concepts, using the die as the package.

To ensure the high-impedance state during power up or power down, OE should be tied to V<sub>CC</sub> through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

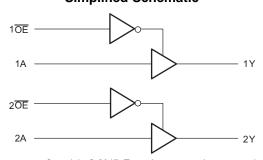
This device is fully specified for partial-power-down applications using Ioff. The Ioff circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down.

#### Device Information<sup>(1)</sup>

PART NUMBER	PACKAGE	BODY SIZE
SN74LVC2G125DCTR	SM8 (8)	2.95 mm × 2.80 mm
SN74LVC2G125DCUR	VSSOP (8)	2.30 mm × 2.00 mm
SN74LVC2G125YZPR	DSBGA (8)	1.91 mm × 0.91 mm

(1) For all available packages, see the orderable addendum at the end of the data sheet.

## Simplified Schematic



Copyright © 2017, Texas Instruments Incorporated



#### **Table of Contents**

1	Features 1	8.2 Functional Block Diagram	10
2	Applications 1	8.3 Feature Description1	10
3	Description 1	8.4 Device Functional Modes	11
4	Revision History2	9 Application and Implementation 1	12
5	Pin Configuration and Functions 4	9.1 Application Information	12
6	Specifications5	9.2 Typical Application1	12
U	6.1 Absolute Maximum Ratings	10 Power Supply Recommendations 1	13
	6.2 ESD Ratings	11 Layout 1	13
	6.3 Recommended Operating Conditions	11.1 Layout Guidelines 1	13
	6.4 Thermal Information	11.2 Layout Example	14
	6.5 Electrical Characteristics	12 Device and Documentation Support 1	15
	6.6 Switching Characteristics: $T_A = -40^{\circ}\text{C to } +85^{\circ}\text{C } \dots$ 7	12.1 Documentation Support	
	6.7 Switching Characteristics: T <sub>A</sub> = -40°C to +125°C 7	12.2 Receiving Notification of Documentation Updates 1	15
	6.8 Operating Characteristics	12.3 Community Resources	15
	6.9 Typical Characteristics	12.4 Trademarks1	15
7	Parameter Measurement Information 9	12.5 Electrostatic Discharge Caution 1	15
8	Detailed Description	12.6 Glossary1	15
•	8.1 Overview	13 Mechanical, Packaging, and Orderable Information1	15

## 4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Cł	nanges from Revision P (January 2016) to Revision Q	Page
•	Removed '200-V Machine Model' from Features for consistency with ESD ratings table.	1
•	Added orderable part numbers associated with each package. Changed US8 to VSSOP	1
•	Updated YZP package drawing to match mechanical drawing pinout.	4
•	Added YZP pin identifiers to Pin Function table. Added 'buffer #' to Description for pins 2, 3, 5, and 6. Changed 'Power pin' to 'Positive supply'	4
•	Added updated package thermal values based on new models. Changes: $R_{\theta JA}$ DCT 220 -> 199.0, DCU 227 -> 217.8, YZP 102 -> 99.8. Added: $R_{\theta JCtop}$ , $R_{\theta JB}$ , $\psi_{JT}$ , $\psi_{JB}$	6
•	Added 'Balanced Push-Pull Outputs,' 'CMOS Inputs,' 'Clamp Diodes,' 'Partial Power Down, 'Over-voltage Tolerant Inputs.' Removed bullet list	10
•	Added improved layout guidelines and trace example image.	13
•	Added Documentation Support section, Receiving Notification of Documentation Updates section, and Community Resources section	15
Cł	nanges from Revision O (January 2015) to Revision P	Page
•	Added overbar for active low to 1 OE and 2 OE to the Simplified Schematic	1
•	Added T <sub>J</sub> Junction temperature to the <i>Absolute Maximum Ratings</i>	5
•	Added overbar for active low to 1 OE and 2 OE to the Functional Block Diagram	

## Changes from Revision N (November 2013) to Revision O

Added Applications, Device Information table, Pin Functions table, ESD Ratings table, Thermal Information table, Typical Characteristics, Feature Description section, Device Functional Modes, Application and Implementation section, Power Supply Recommendations section, Layout section, Device and Documentation Support section, and Mechanical, Packaging, and Orderable Information section.

Submit Documentation Feedback

Copyright © 1999–2017, Texas Instruments Incorporated

**Page** 

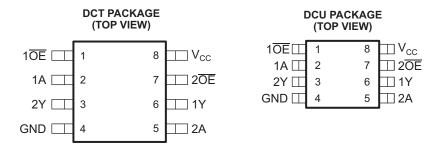




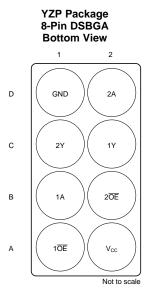
С	hanges from Revision M (January 2007) to Revision N	Page
•	Updated Features	1
•	Updated document to new TI data sheet format	1
•	Removed Ordering Information table.	1
•	Changed MAX operating temperature to 125°C in Recommended Operating Conditions table	6



# 5 Pin Configuration and Functions



See mechanical drawings for dimensions.



See mechanical drawings for dimensions.

#### **Pin Functions**

	PIN		TYPE	DESCRIPTION				
NAME	DCT, DCU	YZP	ITPE	DESCRIPTION				
1A	2	B1	I	Input of buffer 1				
2A	5	D2	I	Input of buffer 2				
1 <del>OE</del>	1	A1	I	Output Enable for buffer 1				
2 <del>OE</del>	7	B2	I	Output Enable for buffer 2				
1Y	6	C2	0	Output of buffer 1				
2Y	3	C1	0	Output of buffer 2				
GND	4	D1	_	Ground				
V <sub>CC</sub>	8	A2	_	Positive supply				



## 6 Specifications

## 6.1 Absolute Maximum Ratings

See<sup>(1)</sup>

			N	IIN	MAX	UNIT
$V_{CC}$	Supply voltage		-	0.5	6.5	V
VI	Input voltage (2)			0.5	6.5	V
Vo	Voltage range applied to any output in the high-impeda	ance or power-off state <sup>(2)</sup>		0.5	6.5	V
Vo				0.5	V <sub>CC</sub> + 0.5	V
I <sub>IK</sub>	Input clamp current	V <sub>I</sub> < 0			-50	mA
I <sub>OK</sub>	Output clamp current	V <sub>O</sub> < 0			<b>-</b> 50	mA
Io	Continuous output current				±50	mA
	Continuous current through V <sub>CC</sub> or GND				±100	mA
$T_{J}$	Junction temperature				150	°C
T <sub>stg</sub>	Storage temperature		_	65	150	°C

<sup>(1)</sup> Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

## 6.2 ESD Ratings

			VALUE	UNIT
.,		Human body model (HBM), per ANSI/ESDA/JEDEC JS-001 (1)	2000	
V <sub>(ESD)</sub>	discharge	Charged device model (CDM), per JEDEC specification JESD22-C101 <sup>(2)</sup>	1000	V

<sup>(1)</sup> JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

<sup>(2)</sup> The input negative-voltage and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

<sup>(3)</sup> The value of V<sub>CC</sub> is provided in the *Recommended Operating Conditions* table.

<sup>(2)</sup> JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.



## 6.3 Recommended Operating Conditions

over recommended operating free-air temperature range (unless otherwise noted)(1)

			MIN	MAX	UNIT
.,	0 1 1	Operating	1.65	5.5	.,
V <sub>CC</sub>	Supply voltage	Data retention only	1.5		V
		V <sub>CC</sub> = 1.65 V to 1.95 V	0.65 × V <sub>CC</sub>		
.,	High level in a decidence	V <sub>CC</sub> = 2.3 V to 2.7 V	1.7		V
V <sub>IH</sub>	High-level input voltage	V <sub>CC</sub> = 3 V to 3.6 V	2		V
		V <sub>CC</sub> = 4.5 V to 5.5 V	0.7 × V <sub>CC</sub>		
		V <sub>CC</sub> = 1.65 V to 1.95 V		0.35 × V <sub>CC</sub>	
. ,	Law law library walkana	V <sub>CC</sub> = 2.3 V to 2.7 V		0.7	.,
$V_{IL}$	Low-level input voltage	V <sub>CC</sub> = 3 V to 3.6 V		0.8	V
		V <sub>CC</sub> = 4.5 V to 5.5 V		0.3 × V <sub>CC</sub>	
V <sub>I</sub>	Input voltage	·	0	5.5	V
,	Outside the sec	High or low state	0	V <sub>cc</sub>	V
/ <sub>0</sub>	Output voltage	3-state	0	5.5	V
		V <sub>CC</sub> = 1.65 V		-4	
		V <sub>CC</sub> = 2.3 V		-8	
ОН	High-level output current			-16	mA
		V <sub>CC</sub> = 3 V		-24	
		V <sub>CC</sub> = 4.5 V		-32	
		V <sub>CC</sub> = 1.65 V		4	
		V <sub>CC</sub> = 2.3 V		8	
OL	Low-level output current			16	mA
		$V_{CC} = 3 V$		24	
		V <sub>CC</sub> = 4.5 V		32	
		$V_{CC} = 1.8 \text{ V} \pm 0.15 \text{ V}, 2.5 \text{ V} \pm 0.2 \text{ V}$		20	ns/V
∆t/∆v	Input transition rise or fall rate	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$		10	
		$V_{CC} = 5 \text{ V} \pm 0.5 \text{ V}$		5	
T <sub>A</sub>	Operating free-air temperature		-40	125	°C

All unused inputs of the device must be held at V<sub>CC</sub> or GND to ensure proper device operation. See Implications of Slow or Floating CMOS Inputs, SCBA004.

#### 6.4 Thermal Information

0.7 1			SN74LVC2G125		
	THERMAL METRIC <sup>(1)</sup>	DCT (SM8)	DCU (VSSOP)	YZP (DSBGA)	UNIT
		8 PINS	8 PINS	8 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	199.0	217.8	99.8	°C/W
$R_{\theta JCtop}$	Junction-to-case (top) thermal resistance	89.5	98.3	1.0	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	118.7	138.7	29.6	°C/W
ΨЈТ	Junction-to-top characterization parameter	14.3	34.6	0.5	°C/W
ΨЈВ	Junction-to-board characterization parameter	117.4	138.2	29.8	°C/W

<sup>(1)</sup> For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.



#### 6.5 Electrical Characteristics

over recommended operating free-air temperature range (unless otherwise noted)

_	ADAMETED	TEST CONDITIONS		.,	$T_A = -40$	°C to +85°C		$T_A = -40$	UNIT		
Ρ.	ARAMETER	TEST CONDITIONS	•	V <sub>cc</sub>	MIN	TYP <sup>(1)</sup>	MAX	MIN	TYP <sup>(1)</sup>	MAX	UNII
		I <sub>OH</sub> = -100 μA		1.65 V to 5.5 V	V <sub>CC</sub> - 0.1			V <sub>CC</sub> - 0.1			
		$I_{OH} = -4 \text{ mA}$		1.65 V	1.2			1.2			
				1.8 V	1.4						
V <sub>OH</sub>		$I_{OH} = -8 \text{ mA}$		2.3 V	1.9			1.9			V
		$I_{OH} = -16 \text{ mA}$		3 V	2.4			2.4			
	I <sub>OH</sub> = -24 mA		3 V	2.3			2.3				
		$I_{OH} = -32 \text{ mA}$		4.5 V	3.8			3.8			
V <sub>OL</sub>		I <sub>OL</sub> = 100 μA		1.65 V to 5.5 V			0.1			0.1	
		I <sub>OL</sub> = 4 mA		1.65 V			0.45			0.45	
		1 0 m A		1.8 V			0.45				
		I <sub>OL</sub> = 8 mA		2.3 V			0.3			0.3	V
		I <sub>OL</sub> = 16 mA	3 V			0.4			0.4		
		I <sub>OL</sub> = 24 mA		3 V			0.55			0.55	
		I <sub>OL</sub> = 32 mA		4.5 V			0.55			0.75	
l <sub>l</sub>	A or <del>OE</del> inputs	V <sub>I</sub> = 5.5 V or GND		0 to 5.5 V			±5			±5	μΑ
I <sub>off</sub>		V <sub>I</sub> or V <sub>O</sub> = 5.5 V		0			±10			±10	μA
loz		V <sub>O</sub> = 0 to 5.5 V		3.6 V			10			10	μA
I <sub>CC</sub>		$V_I = 5.5 \text{ V or GND},$	I <sub>O</sub> = 0	1.65 V to 5.5 V			10			10	μΑ
Δl <sub>CC</sub>		One input at $V_{CC}$ – 0.6 V, Other inputs at $V_{CC}$ or GND		3 V to 5.5 V			500			500	μA
	Data inputs	V V or CND		221/		3.5			3.5		~F
Ci	Control inputs	$V_I = V_{CC}$ or GND	3.3 V		4			4	pF		
Co		$V_O = V_{CC}$ or GND		3.3 V		6.5			6.5		pF

<sup>(1)</sup> All typical values are at  $V_{CC}$  = 3.3 V,  $T_A$  = 25°C.

# 6.6 Switching Characteristics: $T_A = -40$ °C to +85°C

over recommended operating free-air temperature range (unless otherwise noted) (see Figure 3)

					T	. = -40°C	to +85°C				
PARAMETER	FROM (INPUT)	TO (OUTPUT)	V <sub>CC</sub> = 1 ± 0.15	I.8 V 5 V	V <sub>CC</sub> = 2 ± 0.2	2.5 V V	V <sub>CC</sub> = 3 ± 0.3	3.3 V 5 V	V <sub>CC</sub> = ± 0.5	5 V V	UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t <sub>pd</sub>	Α	Y	3.3	9.1	1.5	4.8	1.4	4.3	1	3.7	ns
t <sub>en</sub>	ŌĒ	Y	4	9.9	1.9	5.6	1.2	4.7	1.2	3.8	ns
t <sub>dis</sub>	ŌĒ	Υ	1.5	11.6	1	5.8	1.4	4.6	1	3.4	ns

# 6.7 Switching Characteristics: $T_A = -40^{\circ}C$ to +125°C

over recommended operating free-air temperature range (unless otherwise noted) (see Figure 3)

		, ,	`			, ,	•	,			
					T <sub>A</sub>	= -40°C	to +125°C				
PARAMETER	FROM (INPUT)	TO (OUTPUT)	V <sub>CC</sub> = 1 ± 0.15		V <sub>CC</sub> = 2 ± 0.2		V <sub>CC</sub> = 3 ± 0.3		V <sub>CC</sub> = ± 0.5	5 V V	UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t <sub>pd</sub>	A	Υ	3.3	10.1	1.5	5.8	1.4	5.3	1	4.2	ns
t <sub>en</sub>	ŌĒ	Υ	4	10.9	1.9	6.6	1.2	5.7	1.2	4.3	ns
t <sub>dis</sub>	ŌĒ	Υ	1.5	12.6	1	6.8	1.4	5.6	1	3.9	ns

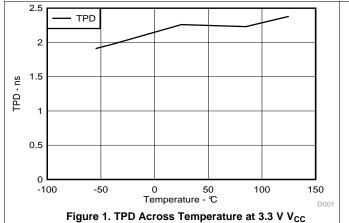


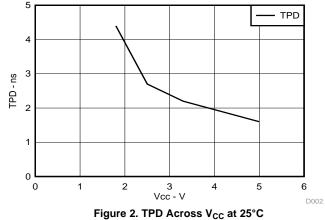
# 6.8 Operating Characteristics

 $T_A = 25^{\circ}$ 

PARAMETER			TEST CONDITIONS	V <sub>CC</sub> = 1.8 V TYP	V <sub>CC</sub> = 2.5 V TYP	V <sub>CC</sub> = 3.3 V TYP	V <sub>CC</sub> = 5 V TYP	UNIT
C	Power dissipation	Outputs enabled	f = 10 MHz	19	19	20	22	pF
C <sub>pd</sub>	capacitance	Outputs disabled	1 = 10 WHZ	2	2	2	3	þΓ

# 6.9 Typical Characteristics



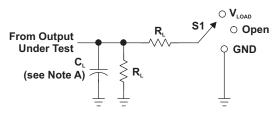


Submit Documentation Feedback

Copyright © 1999–2017, Texas Instruments Incorporated



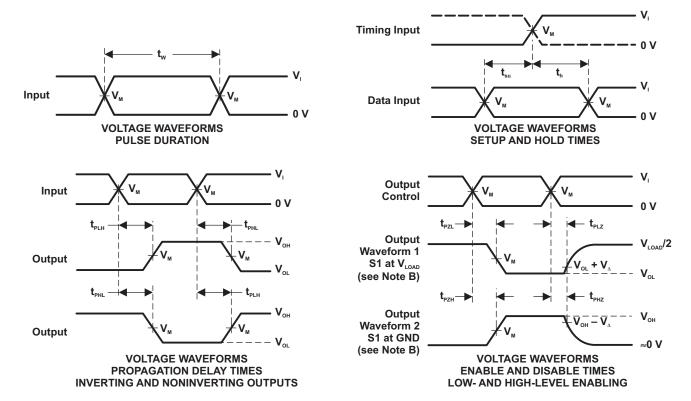
#### 7 Parameter Measurement Information



TEST	S1
t <sub>PLH</sub> /t <sub>PHL</sub>	Open
t <sub>PLZ</sub> /t <sub>PZL</sub>	<b>V</b> <sub>LOAD</sub>
t <sub>PHZ</sub> /t <sub>PZH</sub>	GND

**LOAD CIRCUIT** 

.,	INPUTS			.,			.,
V <sub>cc</sub>	V,	t,/t,	V <sub>M</sub>	<b>V</b> <sub>LOAD</sub>	C <sub>L</sub>	R <sub>⊾</sub>	V <sub>A</sub>
1.8 V ± 0.15 V	V <sub>cc</sub>	≤2 ns	V <sub>cc</sub> /2	2 × V <sub>cc</sub>	30 pF	<b>1 k</b> Ω	0.15 V
2.5 V ± 0.2 V	V <sub>cc</sub>	≤2 ns	V <sub>cc</sub> /2	2 × V <sub>cc</sub>	30 pF	<b>500</b> Ω	0.15 V
3.3 V ± 0.3 V	3 V	≤2.5 ns	1.5 V	6 V	50 pF	500 Ω	0.3 V
5 V ± 0.5 V	V <sub>cc</sub>	≤2.5 ns	V <sub>cc</sub> /2	2 × V <sub>cc</sub>	50 pF	<b>500</b> Ω	0.3 V



NOTES: A. C, includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR  $\leq$  10 MHz,  $Z_{o}$  = 50  $\Omega$ .
- D. The outputs are measured one at a time, with one transition per measurement.
- E.  $t_{\text{PLZ}}$  and  $\dot{t}_{\text{PHZ}}$  are the same as  $t_{\text{dis}}$ .
- F.  $t_{\mbox{\tiny PZL}}$  and  $t_{\mbox{\tiny PZH}}$  are the same as  $t_{\mbox{\tiny en}}.$
- G.  $t_{PlH}$  and  $t_{PHl}$  are the same as  $t_{pd}$ .
- H. All parameters and waveforms are not applicable to all devices.

Figure 3. Load Circuit and Voltage Waveforms

Submit Documentation Feedback

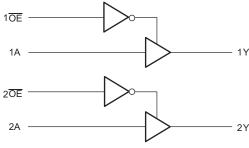


## 8 Detailed Description

#### 8.1 Overview

The SN74LVC2G125 device contains dual buffer gate device with output enable control and performs the Boolean function Y = A. This device is fully specified for partial-power-down applications using  $I_{off}$ . The  $I_{off}$  circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down. To ensure the high-impedance state during power up or power down,  $\overline{OE}$  should be tied to  $V_{CC}$  through a pull-up resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

## 8.2 Functional Block Diagram



Copyright © 2017, Texas Instruments Incorporated

## 8.3 Feature Description

#### 8.3.1 Balanced High-Drive CMOS Push-Pull Outputs

A balanced output allows the device to sink and source similar currents. The high drive capability of this device creates fast edges into light loads so routing and load conditions should be considered to prevent ringing. Additionally, the outputs of this device are capable of driving larger currents than the device can sustain without being damaged. It is important for the power output of the device to be limited to avoid thermal runaway and damage due to over-current. The electrical and thermal limits defined the in the *Absolute Maximum Ratings* must be followed at all times.

#### 8.3.2 Standard CMOS Inputs

Standard CMOS inputs are high impedance and are typically modelled as a resistor in parallel with the input capacitance given in the *Electrical Characteristics*. The worst case resistance is calculated with the maximum input voltage, given in the *Absolute Maximum Ratings*, and the maximum input leakage current, given in the *Electrical Characteristics*, using ohm's law  $(R = V \div I)$ .

Signals applied to the inputs need to have fast edge rates, as defined by  $\Delta t/\Delta v$  in *Recommended Operating Conditions* to avoid excessive currents and oscillations. If a slow or noisy input signal is required, a device with a Schmitt-trigger input should be utilized to condition the input signal prior to the standard CMOS input.

#### 8.3.3 Clamp Diodes

The inputs and outputs to this device have negative clamping diodes.

## **CAUTION**

Voltages beyond the values specified in the *Absolute Maximum Ratings* table can cause damage to the device. The input negative-voltage and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

Submit Documentation Feedback



## **Feature Description (continued)**

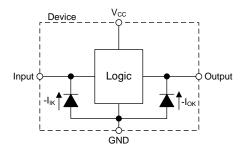


Figure 4. Electrical Placement of Clamping Diodes for Each Input and Output

#### 8.3.4 Partial Power Down (Ioff)

The inputs and outputs for this device enter a high impedance state when the supply voltage is 0 V. The maximum leakage into or out of any input or output pin on the device is specified by I<sub>off</sub> in the *Electrical Characteristics*.

## 8.3.5 Over-voltage Tolerant Inputs

Input signals to this device can be driven above the supply voltage so long as they remain below the maximum input voltage value specified in the *Absolute Maximum Ratings* .

#### 8.4 Device Functional Modes

Table 1 lists the functional modes of the SN74LVC2G125.

**Table 1. Function Table** 

INP	JTS	OUTPUT
ŌĒ	Α	Υ
L	Н	Н
L	L	L
Н	X	Z



## 9 Application and Implementation

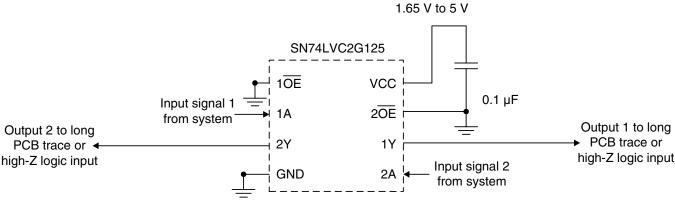
#### NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

## 9.1 Application Information

The SN74LVC2G125 device is a high drive CMOS device that can be used as a output enabled buffer with a high output drive, such as an LED application. It can produce 24 mA of drive current at 3.3 V making it Ideal for driving multiple outputs and good for high speed applications up to 100 MHz. The inputs are 5.5-V tolerant allowing it to translate down to  $V_{\rm CC}$ .

## 9.2 Typical Application



Copyright © 2017, Texas Instruments Incorporated

Figure 5. Typical Application Schematic

#### 9.2.1 Design Requirements

This device uses CMOS technology and has balanced output drive. Take care to avoid bus contention because it can drive currents that would exceed maximum limits. The high drive also creates fast edges into light loads so routing and load conditions should be considered to prevent ringing.

## 9.2.2 Detailed Design Procedure

- 1. Recommended Input Conditions:
  - For rise time and fall time specifications, see ( $\Delta t/\Delta V$ ) in the Recommended Operating Conditions table.
  - For specified high and low levels, see (V<sub>IH</sub> and V<sub>IL</sub>) in the Recommended Operating Conditions table.
  - Inputs are overvoltage tolerant allowing them to go as high as (V<sub>I</sub> max) in the Recommended Operating
     Conditions table at any valid V<sub>CC</sub>.

#### 2. Recommended Output Conditions:

- Load currents should not exceed (I<sub>O</sub> max) per output and should not exceed (Continuous current through V<sub>CC</sub> or GND) total current for the part. These limits are located in the *Absolute Maximum Ratings* table.
- Outputs should not be pulled above V<sub>CC</sub>.

Submit Documentation Feedback

Copyright © 1999–2017, Texas Instruments Incorporated



## Typical Application (continued)

#### 9.2.3 Application Curve

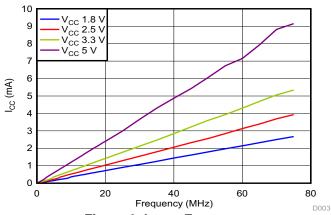


Figure 6. I<sub>CC</sub> vs Frequency

## 10 Power Supply Recommendations

The power supply can be any voltage between the min and max supply voltage rating located in the Recommended Operating Conditions table.

Each V<sub>CC</sub> pin should have a good bypass capacitor to prevent power disturbance. For devices with a single supply a  $0.1-\mu F$  capacitor is recommended and if there are multiple  $V_{CC}$  pins then a  $0.01-\mu F$  or  $0.022-\mu F$ capacitor is recommended for each power pin. It is ok to parallel multiple bypass caps to reject different frequencies of noise. 0.1-μF and 1-μF capacitors are commonly used in parallel. The bypass capacitor should be installed as close to the power pin as possible for best results.

#### Layout 11

#### 11.1 Layout Guidelines

Copyright © 1999-2017, Texas Instruments Incorporated

When using multiple bit logic devices, inputs should not float. In many cases, functions or parts of functions of digital logic devices are unused. Some examples are when only two inputs of a triple-input AND gate are used, or when only 3 of the 4-buffer gates are used. Such input pins should not be left unconnected because the undefined voltages at the outside connections result in undefined operational states.

Specified in Figure 7 are rules that must be observed under all circumstances. All unused inputs of digital logic devices must be connected to a high or low bias to prevent them from floating. The logic level that should be applied to any particular unused input depends on the function of the device. Generally they will be tied to GND or  $V_{\text{CC}}$ , whichever makes more sense or is more convenient.

Even low data rate digital signals can have high frequency signal components due to fast edge rates. When a PCB trace turns a corner at a 90° angle, a reflection can occur. A reflection occurs primarily because of the change of width of the trace. At the apex of the turn, the trace width increases to 1.414 times the width. This increase upsets the transmission-line characteristics, especially the distributed capacitance and self-inductance of the trace which results in the reflection. Not all PCB traces can be straight and therefore some traces must turn corners. Figure 8 shows progressively better techniques of rounding corners. Only the last example (BEST) maintains constant trace width and minimizes reflections.



# 11.2 Layout Example



Figure 7. Proper multi-gate input termination diagram

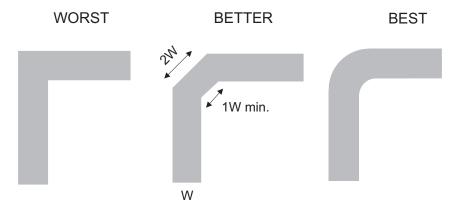


Figure 8. Trace Example

Submit Documentation Feedback



## 12 Device and Documentation Support

## 12.1 Documentation Support

#### 12.1.1 Related Documentation

For related documentation see the following:

Implications of Slow or Floating CMOS Inputs, SCBA004.

## 12.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. In the upper right corner, click on Alert me to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

#### 12.3 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

TI E2E™ Online Community TI's Engineer-to-Engineer (E2E) Community. Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

Design Support TI's Design Support Quickly find helpful E2E forums along with design support tools and contact information for technical support.

#### 12.4 Trademarks

NanoFree, E2E are trademarks of Texas Instruments.

#### 12.5 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

#### 12.6 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms, and definitions.

## Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

Copyright © 1999-2017, Texas Instruments Incorporated

www.ti.com

21-Nov-2022

#### **PACKAGING INFORMATION**

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
74LVC2G125DCTRE4	ACTIVE	SM8	DCT	8	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	C25 (R, Z)	Samples
74LVC2G125DCTRE6	ACTIVE	SM8	DCT	8	3000	RoHS & Non-Green	SNBI	Level-1-260C-UNLIM	-40 to 125	C25 Z	Samples
74LVC2G125DCTRG4	ACTIVE	SM8	DCT	8	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	C25 (R, Z)	Samples
74LVC2G125DCURE4	ACTIVE	VSSOP	DCU	8	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	C25R	Samples
74LVC2G125DCURG4	ACTIVE	VSSOP	DCU	8	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	C25R	Samples
74LVC2G125DCUTG4	ACTIVE	VSSOP	DCU	8	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	C25R	Samples
SN74LVC2G125DCT3	ACTIVE	SM8	DCT	8	3000	RoHS & Non-Green	SNBI	Level-1-260C-UNLIM	-40 to 125	C25 Z	Samples
SN74LVC2G125DCTR	ACTIVE	SM8	DCT	8	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	C25 (R, Z)	Samples
SN74LVC2G125DCU3	ACTIVE	VSSOP	DCU	8	3000	RoHS & Non-Green	SNBI	Level-1-260C-UNLIM	-40 to 125	25 CZ	Samples
SN74LVC2G125DCUR	ACTIVE	VSSOP	DCU	8	3000	RoHS & Green	NIPDAU   SN	Level-1-260C-UNLIM	-40 to 125	(25, C25J, C25Q, C 25R) CZ	Samples
SN74LVC2G125DCUT	ACTIVE	VSSOP	DCU	8	250	RoHS & Green	NIPDAU   SN	Level-1-260C-UNLIM	-40 to 125	(C25J, C25Q, C25R)	Samples
SN74LVC2G125YZPR	ACTIVE	DSBGA	YZP	8	3000	RoHS & Green	SNAGCU	Level-1-260C-UNLIM	-40 to 125	(CM7, CMN)	Samples

<sup>(1)</sup> The marketing status values are defined as follows: **ACTIVE:** Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW**: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

<sup>(2)</sup> RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

PACKAGE OPTION ADDENDUM

www.ti.com 21-Nov-2022

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

**Important Information and Disclaimer:** The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

#### OTHER QUALIFIED VERSIONS OF SN74LVC2G125:

Automotive: SN74LVC2G125-Q1

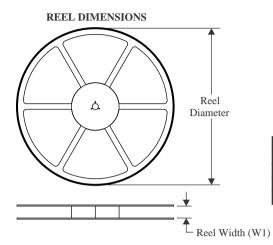
NOTE: Qualified Version Definitions:

• Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects



www.ti.com 28-Nov-2022

## TAPE AND REEL INFORMATION



# TAPE DIMENSIONS + K0 - P1 - B0 W Cavity - A0 -

A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

#### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE

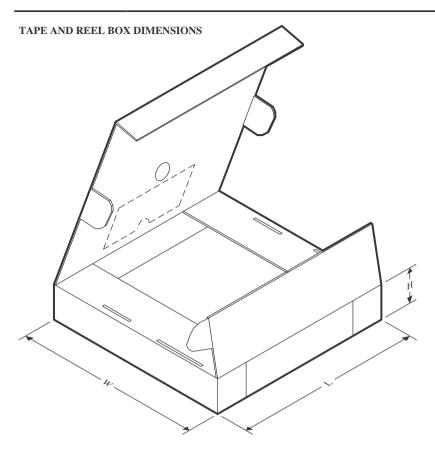


#### \*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
74LVC2G125DCTRE6	SM8	DCT	8	3000	180.0	13.0	3.35	4.5	1.55	4.0	12.0	Q3
74LVC2G125DCURG4	VSSOP	DCU	8	3000	180.0	8.4	2.25	3.35	1.05	4.0	8.0	Q3
74LVC2G125DCUTG4	VSSOP	DCU	8	250	180.0	8.4	2.25	3.35	1.05	4.0	8.0	Q3
SN74LVC2G125DCT3	SM8	DCT	8	3000	180.0	13.0	3.35	4.5	1.55	4.0	12.0	Q3
SN74LVC2G125DCTR	SM8	DCT	8	3000	180.0	13.0	3.35	4.5	1.55	4.0	12.0	Q3
SN74LVC2G125DCTR	SM8	DCT	8	3000	177.8	12.4	3.45	4.4	1.45	4.0	12.0	Q3
SN74LVC2G125DCUR	VSSOP	DCU	8	3000	178.0	9.0	2.25	3.35	1.05	4.0	8.0	Q3
SN74LVC2G125DCUT	VSSOP	DCU	8	250	178.0	9.0	2.25	3.35	1.05	4.0	8.0	Q3
SN74LVC2G125YZPR	DSBGA	YZP	8	3000	178.0	9.2	1.02	2.02	0.63	4.0	8.0	Q1



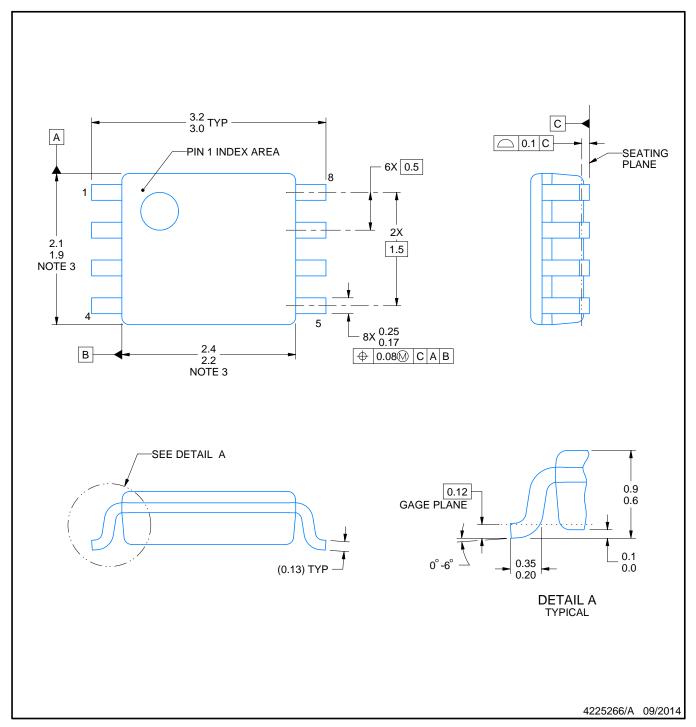
www.ti.com 28-Nov-2022



\*All dimensions are nominal

7 til dilliciololio ale Hollina							
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
74LVC2G125DCTRE6	SM8	DCT	8	3000	182.0	182.0	20.0
74LVC2G125DCURG4	VSSOP	DCU	8	3000	202.0	201.0	28.0
74LVC2G125DCUTG4	VSSOP	DCU	8	250	202.0	201.0	28.0
SN74LVC2G125DCT3	SM8	DCT	8	3000	182.0	182.0	20.0
SN74LVC2G125DCTR	SM8	DCT	8	3000	182.0	182.0	20.0
SN74LVC2G125DCTR	SM8	DCT	8	3000	183.0	183.0	20.0
SN74LVC2G125DCUR	VSSOP	DCU	8	3000	180.0	180.0	18.0
SN74LVC2G125DCUT	VSSOP	DCU	8	250	180.0	180.0	18.0
SN74LVC2G125YZPR	DSBGA	YZP	8	3000	220.0	220.0	35.0





#### NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

  2. This drawing is subject to change without notice.

  3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
  4. Reference JEDEC registration MO-187 variation CA.

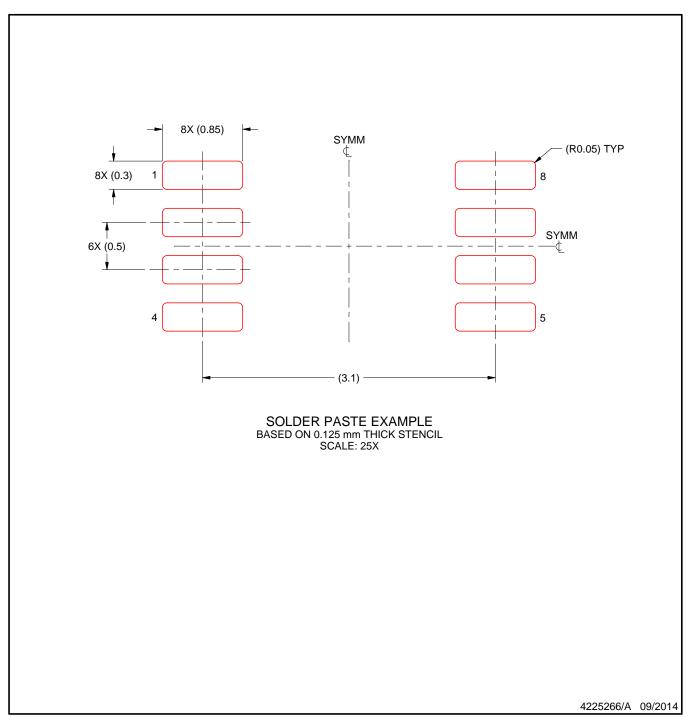




NOTES: (continued)

- 5. Publication IPC-7351 may have alternate designs.
- 6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



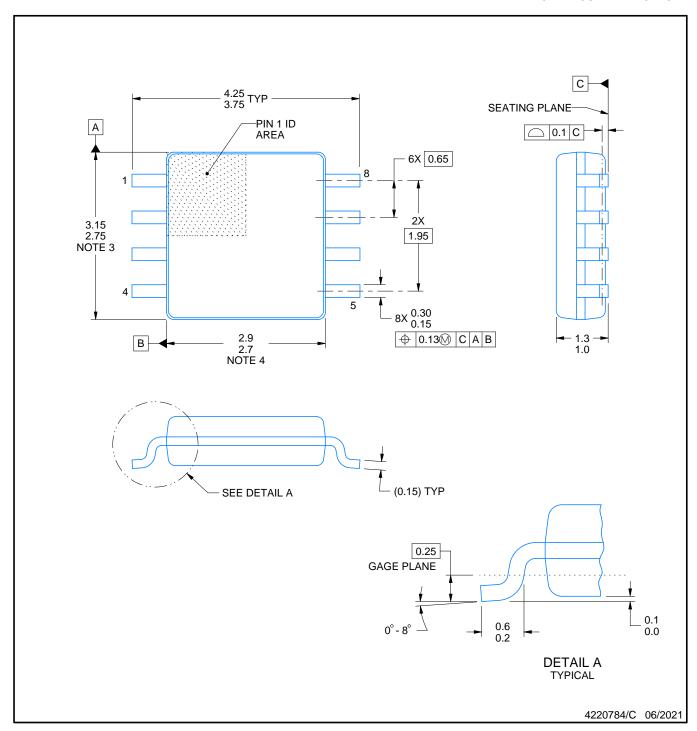


NOTES: (continued)

- 7. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 8. Board assembly site may have different recommendations for stencil design.







#### NOTES:

- 1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

  2. This drawing is subject to change without notice.

  3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.





NOTES: (continued)

5. Publication IPC-7351 may have alternate designs.6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.





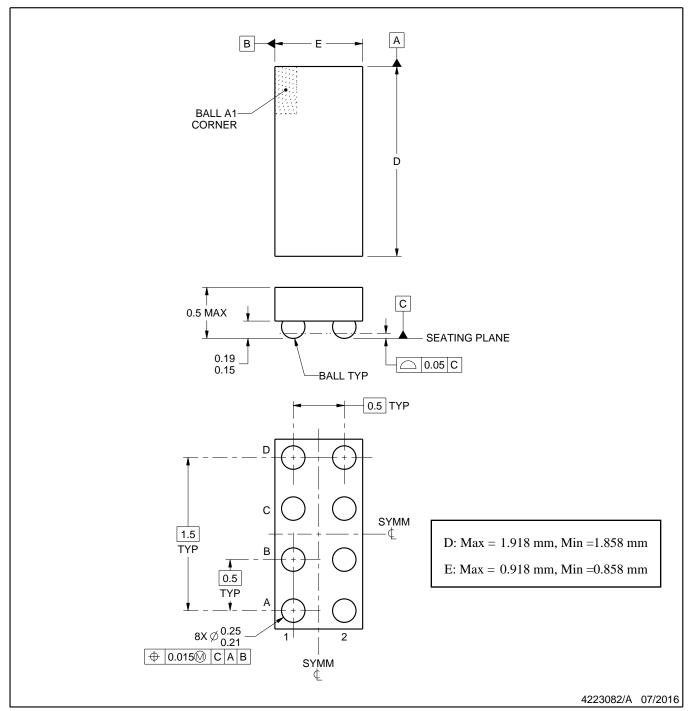
NOTES: (continued)

- 7. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 8. Board assembly site may have different recommendations for stencil design.





DIE SIZE BALL GRID ARRAY

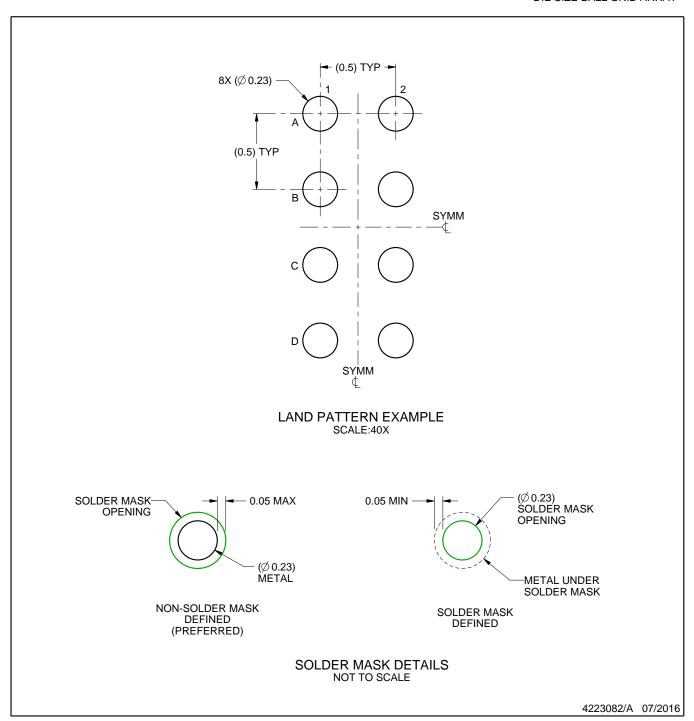


#### NOTES:

- All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.



DIE SIZE BALL GRID ARRAY

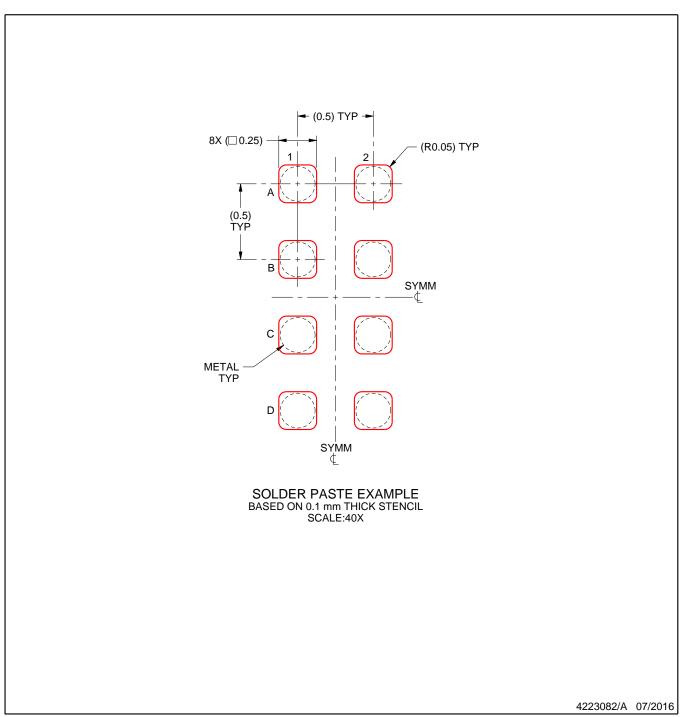


NOTES: (continued)

3. Final dimensions may vary due to manufacturing tolerance considerations and also routing constraints. For more information, see Texas Instruments literature number SNVA009 (www.ti.com/lit/snva009).



DIE SIZE BALL GRID ARRAY



NOTES: (continued)

4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release.



## IMPORTANT NOTICE AND DISCLAIMER

TI PROVIDES TECHNICAL AND RELIABILITY DATA (INCLUDING DATA SHEETS), DESIGN RESOURCES (INCLUDING REFERENCE DESIGNS), APPLICATION OR OTHER DESIGN ADVICE, WEB TOOLS, SAFETY INFORMATION, AND OTHER RESOURCES "AS IS" AND WITH ALL FAULTS, AND DISCLAIMS ALL WARRANTIES, EXPRESS AND IMPLIED, INCLUDING WITHOUT LIMITATION ANY IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE OR NON-INFRINGEMENT OF THIRD PARTY INTELLECTUAL PROPERTY RIGHTS.

These resources are intended for skilled developers designing with TI products. You are solely responsible for (1) selecting the appropriate TI products for your application, (2) designing, validating and testing your application, and (3) ensuring your application meets applicable standards, and any other safety, security, regulatory or other requirements.

These resources are subject to change without notice. TI grants you permission to use these resources only for development of an application that uses the TI products described in the resource. Other reproduction and display of these resources is prohibited. No license is granted to any other TI intellectual property right or to any third party intellectual property right. TI disclaims responsibility for, and you will fully indemnify TI and its representatives against, any claims, damages, costs, losses, and liabilities arising out of your use of these resources.

TI's products are provided subject to TI's Terms of Sale or other applicable terms available either on ti.com or provided in conjunction with such TI products. TI's provision of these resources does not expand or otherwise alter TI's applicable warranties or warranty disclaimers for TI products.

TI objects to and rejects any additional or different terms you may have proposed.

Mailing Address: Texas Instruments, Post Office Box 655303, Dallas, Texas 75265 Copyright © 2023, Texas Instruments Incorporated

# **X-ON Electronics**

Largest Supplier of Electrical and Electronic Components

Click to view similar products for Buffers & Line Drivers category:

Click to view products by Texas Instruments manufacturer:

Other Similar products are found below:

LXV200-024SW 74AUP2G34FW3-7 HEF4043BP NL17SG125DFT2G NLU1GT126CMUTCG CD4041UBE 54FCT240CTDB

74HCT540N DS14C88N 070519XB NL17SZ07P5T5G 74LVC2G17FW4-7 CD4502BE 5962-8982101PA 61446R00 NL17SH17P5T5G

NLV37WZ17USG 74HCT126T14-13 74VHC9126FT(BJ) RHRXH162244K1 74AUP1G34FW5-7 74AUP1G07FW5-7 74LVC1G126FW4-7

74LVC2G126RA3-7 74LVCE1G125FZ4-7 54FCT240TLB NLX3G16DMUTCG NLX2G06AMUTCG LE87100NQCT LE87285NQC

LE87290YQC LE87290YQCT 74AUP1G125FW5-7 NLU2G16CMUTCG MC74LCX244MN2TWG NL17SG17P5T5G

NLV74HC125ADR2G NLVHCT245ADTR2G NLVVHC1G126DFT2G EL5623IRZ ISL15102AIRZ-T13 ISL1539IRZ-T13

MC100EP17MNG MC74HCT365ADR2G MC74LCX244ADTR2G NL27WZ126US NL37WZ16US NLU1G07MUTCG NLU2G07MUTCG NLX3G17BMX1TCG